

International
IR Rectifier
RADIATION HARDENED
POWER MOSFET
SURFACE MOUNT (LCC-18)

PD - 90881B

IRHE9130
100V, P-CHANNEL
REF: MIL-PRF-19500/630
RAD-Hard™ HEXFET®
MOSFET TECHNOLOGY

Product Summary

Part Number	Radiation Level	R _{DS(on)}	I _D	QPL Part Number
IRHE9130	100K Rads (Si)	0.30Ω	-6.5A	JANSR2N7389U
IRHE93130	300K Rads (Si)	0.30Ω	-6.5A	JANSF2N7389U



LCC - 18

International Rectifier's RAD-Hard™ HEXFET® MOSFET technology provides high performance power MOSFETs for space applications. This technology has over a decade of proven performance and reliability in satellite applications. These devices have been characterized for both Total Dose and Single Event Effects (SEE). The combination of low R_{DS(on)} and low gate charge reduces the power losses in switching applications such as DC to DC converters and motor control. These devices retain all of the well established advantages of MOSFETs such as voltage control, fast switching, ease of paralleling and temperature stability of electrical parameters.

Features:

- Single Event Effect (SEE) Hardened
- Low R_{DS(on)}
- Low Total Gate Charge
- Proton Tolerant
- Simple Drive Requirements
- Ease of Paralleling
- Hermetically Sealed
- Ceramic Package
- Surface Mount
- Light Weight

Absolute Maximum Ratings

Pre-Irradiation

	Parameter		Units
I _D @ V _{GS} = 12V, T _C = 25°C	Continuous Drain Current	-6.5	A
I _D @ V _{GS} = 12V, T _C = 100°C	Continuous Drain Current	-4.1	
I _{DM}	Pulsed Drain Current ①	-26	
P _D @ T _C = 25°C	Max. Power Dissipation	25	W
	Linear Derating Factor	0.2	W/°C
V _{GS}	Gate-to-Source Voltage	±20	V
E _{AS}	Single Pulse Avalanche Energy ②	165	mJ
I _{AR}	Avalanche Current ①	-6.5	A
E _{AR}	Repetitive Avalanche Energy ①	2.5	mJ
dv/dt	Peak Diode Recovery dv/dt ③	-22	V/ns
T _J	Operating Junction	-55 to 150	°C
T _{STG}	Storage Temperature Range		
	Pckg. Mounting Surface Temp.	300 (for 5s)	
	Weight	0.42 (Typical)	g

For footnotes refer to the last page

Electrical Characteristics @ T_j = 25°C (Unless Otherwise Specified)

	Parameter	Min	Typ	Max	Units	Test Conditions
BV _{DSS}	Drain-to-Source Breakdown Voltage	-100	—	—	V	V _{GS} = 0 V, I _D = -1.0mA
ΔBV _{DSS} /ΔT _j	Temperature Coefficient of Breakdown Voltage	—	-0.112	—	V/°C	Reference to 25°C, I _D = -1.0mA
R _{DS(on)}	Static Drain-to-Source On-State Resistance	—	—	0.30 0.35	Ω	V _{GS} = -12V, I _D = -4.1A V _{GS} = -12V, I _D = -6.5A ④
V _{GS(th)}	Gate Threshold Voltage	-2.0	—	-4.0	V	V _{DS} = V _{GS} , I _D = -1.0mA
g _{fs}	Forward Transconductance	2.5	—	—	S (Ω)	V _{DS} > -15V, I _{DS} = -4.1A ④
I _{DSS}	Zero Gate Voltage Drain Current	—	—	-25 -250	μA	V _{DS} = -80V, V _{GS} = 0V V _{DS} = -80V V _{GS} = 0V, T _j = 125°C
I _{GSS}	Gate-to-Source Leakage Forward	—	—	-100	nA	V _{GS} = -20V
I _{GSS}	Gate-to-Source Leakage Reverse	—	—	100	nA	V _{GS} = 20V
Q _g	Total Gate Charge	—	—	45	nC	V _{GS} = -12V, I _D = -6.5A V _{DS} = -50V
Q _{gs}	Gate-to-Source Charge	—	—	10	nC	
Q _{gd}	Gate-to-Drain ('Miller') Charge	—	—	25	nC	
t _{d(on)}	Turn-On Delay Time	—	—	30	ns	V _{DD} = -50V, I _D = -6.5A, R _G = 7.5Ω
t _r	Rise Time	—	—	50		
t _{d(off)}	Turn-Off Delay Time	—	—	70		
t _f	Fall Time	—	—	70		
L _S + L _D	Total Inductance	—	6.1	—	nH	Measured from the center of drain pad to center of source pad
C _{iss}	Input Capacitance	—	1200	—	pF	V _{GS} = 0V, V _{DS} = -25V f = 1.0MHz
C _{oss}	Output Capacitance	—	290	—		
C _{rss}	Reverse Transfer Capacitance	—	76	—		

Source-Drain Diode Ratings and Characteristics

	Parameter	Min	Typ	Max	Units	Test Conditions
I _S	Continuous Source Current (Body Diode)	—	—	-6.5	A	
I _{SM}	Pulse Source Current (Body Diode) ①	—	—	-26		
V _{SD}	Diode Forward Voltage	—	—	-3.0	V	T _J = 25°C, I _S = -6.5A, V _{GS} = 0V ④
t _{rr}	Reverse Recovery Time	—	—	250	nS	T _J = 25°C, I _F = -6.5A, di/dt ≥ -100A/μs V _{DD} ≤ -25V ④
Q _{RR}	Reverse Recovery Charge	—	—	0.74	μC	
t _{on}	Forward Turn-On Time	Intrinsic turn-on time is negligible. Turn-on speed is substantially controlled by L _S + L _D .				

Thermal Resistance

	Parameter	Min	Typ	Max	Units	Test Conditions
R _{thJC}	Junction-to-Case	—	—	5.0	°C/W	
R _{thPCB}	Junction-to-PC Board	—	19	—		Solder to a copper clad PC Board

Note: Corresponding Spice and Saber models are available on the G&S Website.

For footnotes refer to the last page

Radiation Characteristics

IRHE9130

International Rectifier Radiation Hardened MOSFETs are tested to verify their radiation hardness capability. The hardness assurance program at International Rectifier is comprised of two radiation environments. Every manufacturing lot is tested for total ionizing dose (per notes 5 and 6) using the TO-3 package. Both pre- and post-irradiation performance are tested and specified using the same drive circuitry and test conditions in order to provide a direct comparison.

Table 1. Electrical Characteristics @ Tj = 25°C, Post Total Dose Irradiation ⑤⑥

	Parameter	100K Rads (Si) ¹		300K Rads (Si) ²		Units	Test Conditions
		Min	Max	Min	Max		
BV _{DSS}	Drain-to-Source Breakdown Voltage	-100	—	-100	—	V	V _{GS} = 0V, I _D = -1.0mA
V _{GS(th)}	Gate Threshold Voltage ④	- 2.0	- 4.0	-2.0	-5.0		V _{GS} = V _{DSS} , I _D = -1.0mA
I _{GSS}	Gate-to-Source Leakage Forward	—	-100	—	-100	nA	V _{GS} = -20V
I _{GSS}	Gate-to-Source Leakage Reverse	—	100	—	100		V _{GS} = 20 V
I _{DSS}	Zero Gate Voltage Drain Current	—	-25	—	-25	μA	V _{DSS} = -80V, V _{GS} = 0V
R _{DS(on)}	Static Drain-to-Source ④ On-State Resistance (TO-3)	—	0.259	—	0.259	Ω	V _{GS} = -12V, I _D = -4.1A
R _{DS(on)}	Static Drain-to-Source ④ On-State Resistance (LCC-18)	—	0.30	—	0.30	Ω	V _{GS} = -12V, I _D = -4.1A
V _{SD}	Diode Forward Voltage ④	—	-3.0	—	-3.0	V	V _{GS} = 0V, I _S = -6.5A

1. Part number IRHE9130 (JANSR2N7389U)

2. Part number IRHE93130 (JANSF2N7389U)

International Rectifier radiation hardened MOSFETs have been characterized in heavy ion environment for Single Event Effects (SEE). Single Event Effects characterization is illustrated in Fig. a and Table 2.

Table 2. Single Event Effect Safe Operating Area

Ion	LET MeV/(mg/cm ²)	Energy (MeV)	Range (μm)	V _{DS} (V)				
				@V _{GS} =0V	@V _{GS} =-5V	@V _{GS} =-10V	@V _{GS} =-15V	@V _{GS} =-20V
Cu	28	285	43	-100	-100	-100	-70	-60
Br	36.8	305	39	-100	-100	-70	-50	-40
I	59.8	343	32.6	-60	—	—	—	—

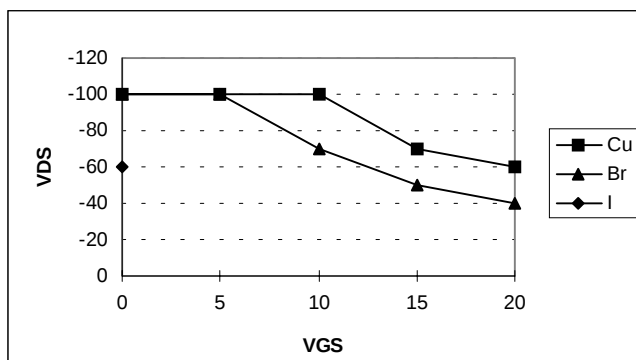


Fig a. Single Event Effect, Safe Operating Area

For footnotes refer to the last page

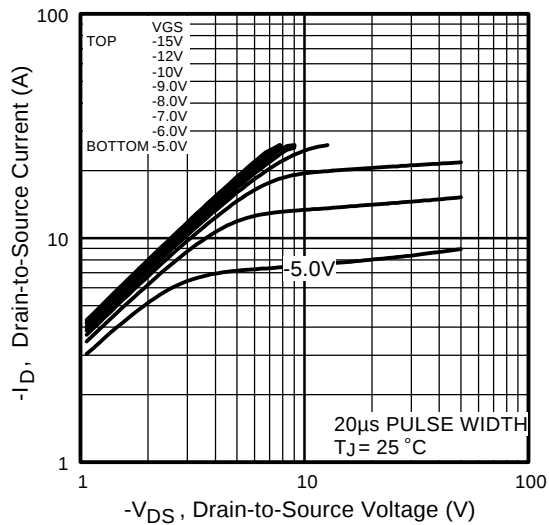


Fig 1. Typical Output Characteristics

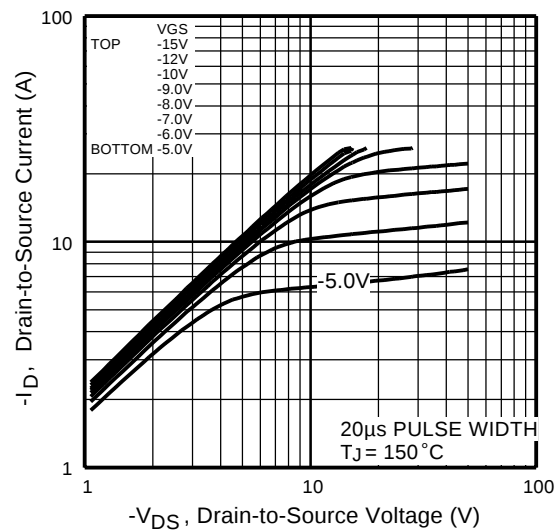


Fig 2. Typical Output Characteristics

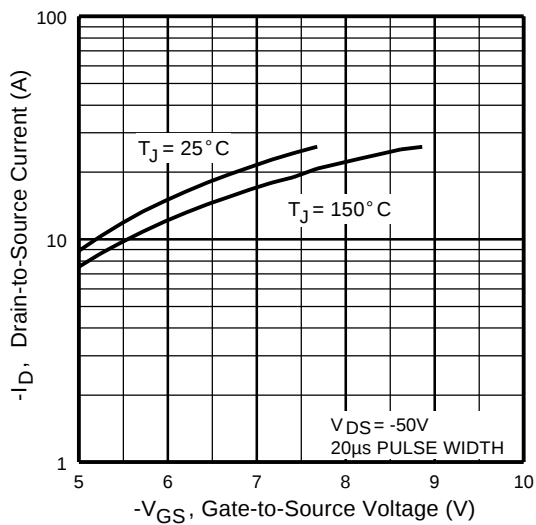


Fig 3. Typical Transfer Characteristics

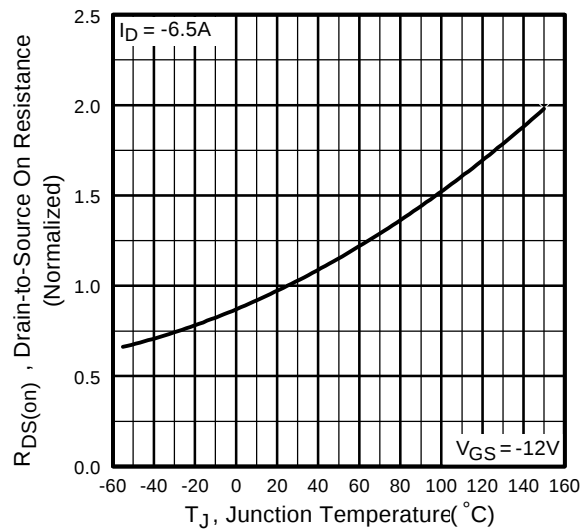


Fig 4. Normalized On-Resistance Vs. Temperature

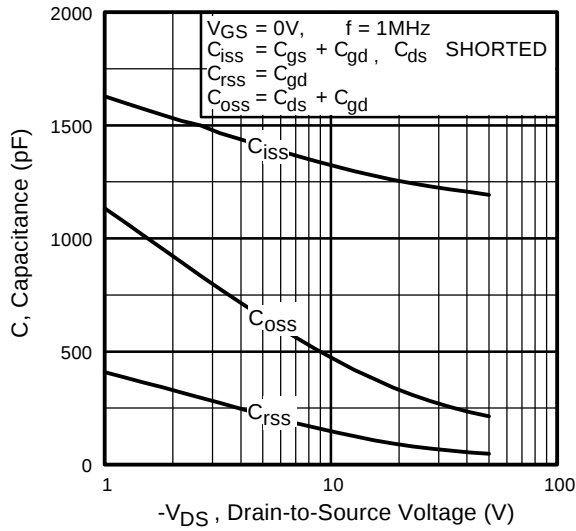


Fig 5. Typical Capacitance Vs. Drain-to-Source Voltage

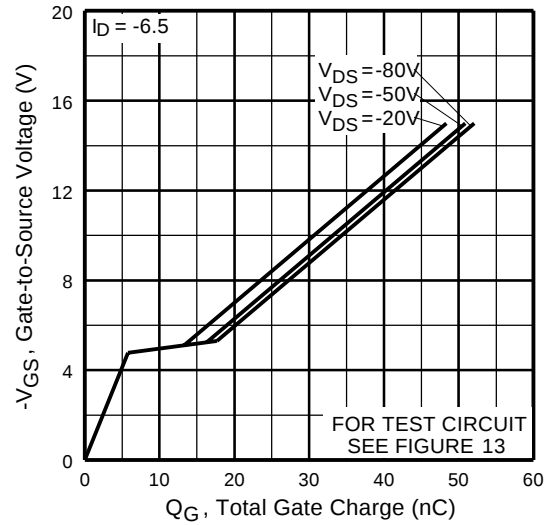


Fig 6. Typical Gate Charge Vs. Gate-to-Source Voltage

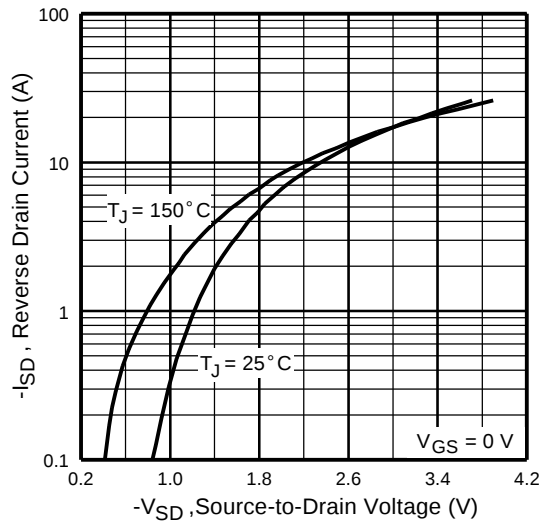


Fig 7. Typical Source-Drain Diode Forward Voltage

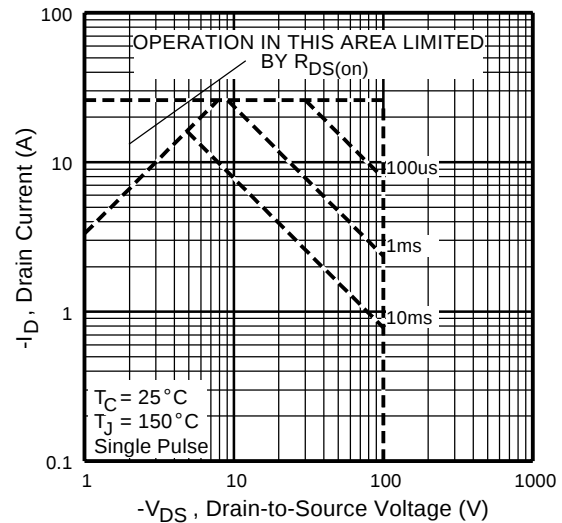


Fig 8. Maximum Safe Operating Area

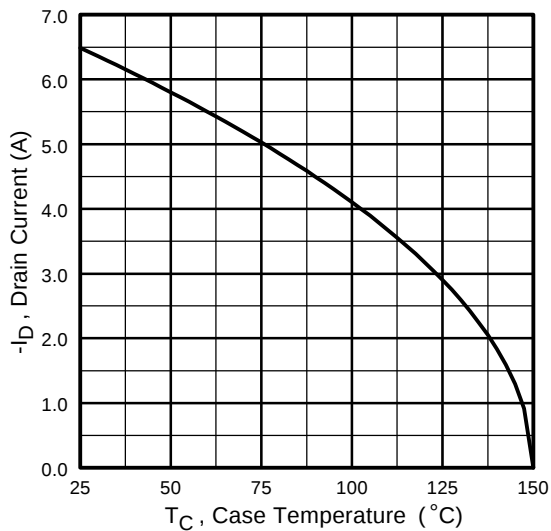


Fig 9. Maximum Drain Current Vs. Case Temperature

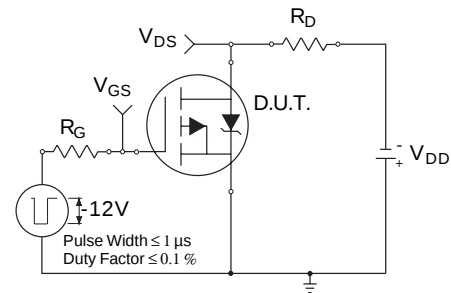


Fig 10a. Switching Time Test Circuit

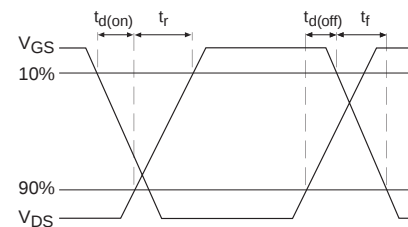


Fig 10b. Switching Time Waveforms

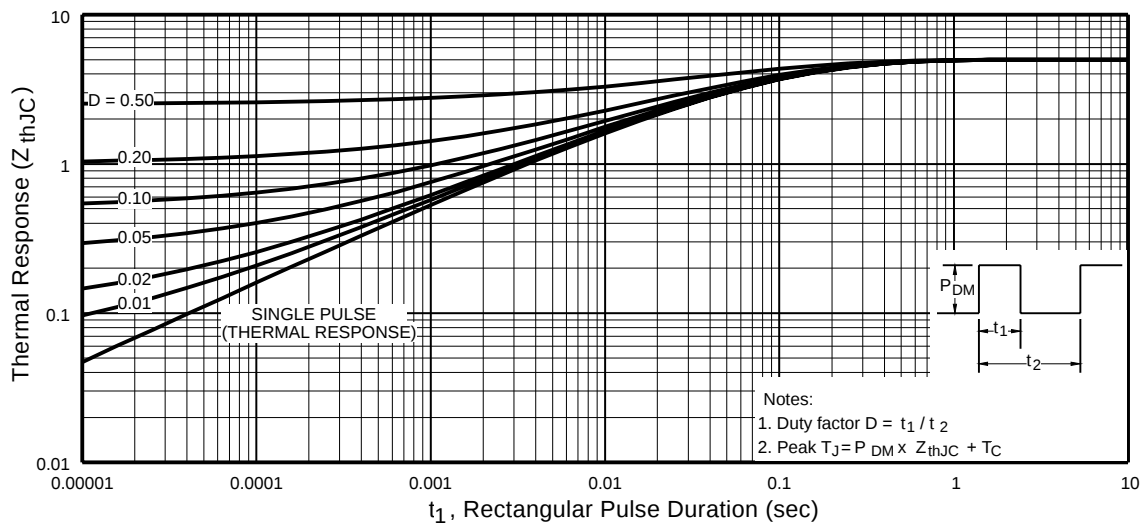


Fig 11. Maximum Effective Transient Thermal Impedance, Junction-to-Case

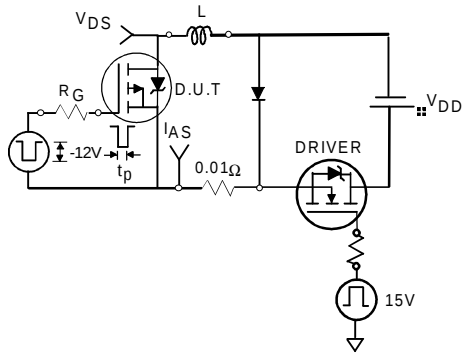


Fig 12a. Unclamped Inductive Test Circuit

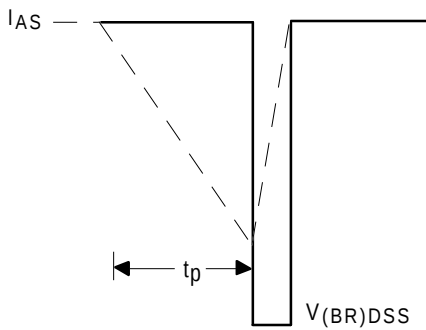


Fig 12b. Unclamped Inductive Waveforms

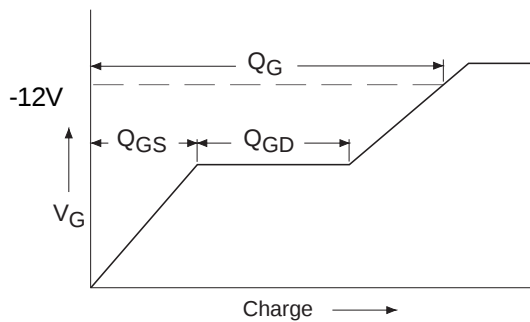


Fig 13a. Basic Gate Charge Waveform

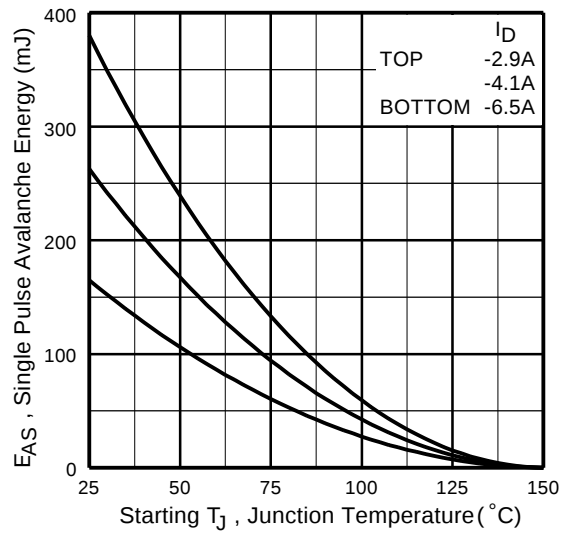


Fig 12c. Maximum Avalanche Energy Vs. Drain Current

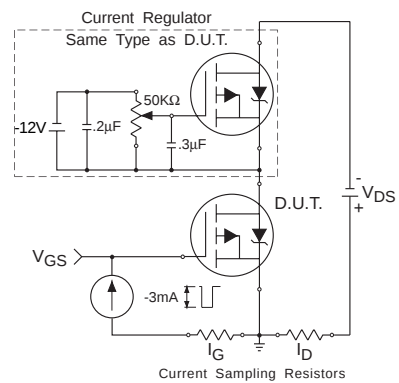
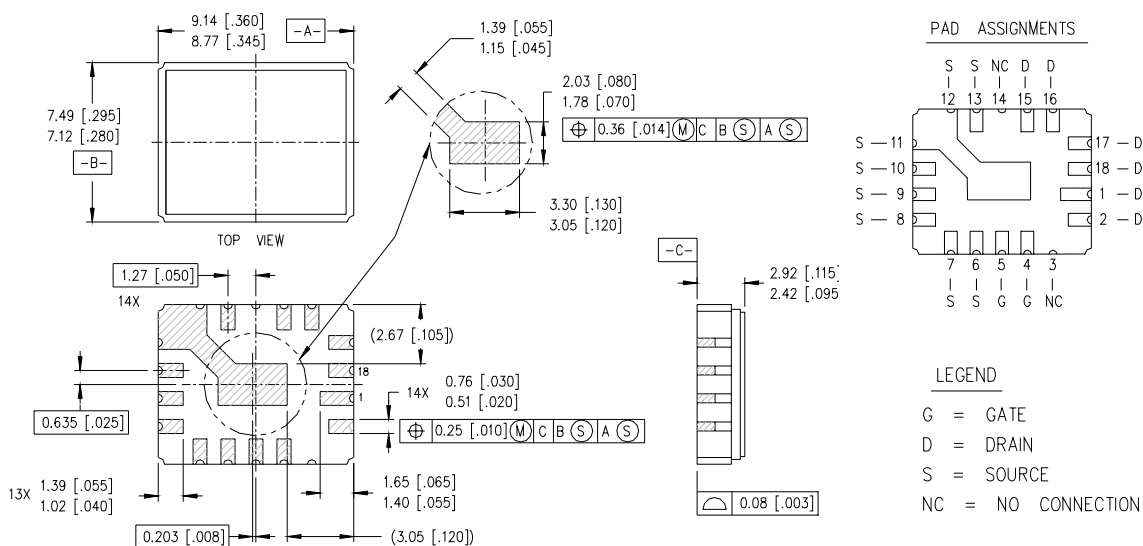


Fig 13b. Gate Charge Test Circuit

Footnotes:

- ① Repetitive Rating; Pulse width limited by maximum junction temperature.
- ② $V_{DD} = -25V$, starting $T_J = 25^\circ C$, $L = 7.8mH$
Peak $I_L = -6.5A$, $V_{GS} = -12V$
- ③ $ISD \leq -6.5A$, $di/dt \leq -430A/\mu s$,
 $V_{DD} \leq -100V$, $T_J \leq 150^\circ C$
- ④ Pulse width $\leq 300 \mu s$; Duty Cycle $\leq 2\%$
- ⑤ **Total Dose Irradiation with V_{GS} Bias.**
12 volt V_{GS} applied and $V_{DS} = 0$ during irradiation per MIL-STD-750, method 1019, condition A.
- ⑥ **Total Dose Irradiation with V_{DS} Bias.**
80 volt V_{DS} applied and $V_{GS} = 0$ during irradiation per MIL-STD-750, method 1019, condition A.

Case Outline and Dimensions — LCC-18



NOTES:

1. DIMENSIONING & TOLERANCING PER ANSI Y14.5M-1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSIONS ARE SHOWN IN MILLIMETERS [INCHES].

International
IR Rectifier

IR WORLD HEADQUARTERS: 233 Kansas St., El Segundo, California 90245, USA Tel: (310) 252-7105
IR EUROPEAN REGIONAL CENTER: 439/445 Godstone Rd, Whyteleafe, Surrey CR3 0BL, UK Tel: ++ 44 (0)20 8645 8000
IR CANADA: 15 Lincoln Court, Brampton, Ontario L6T3Z2, Tel: (905) 453 2200
IR GERMANY: Saalburgstrasse 157, 61350 Bad Homburg Tel: ++ 49 (0) 6172 96590
IR ITALY: Via Liguria 49, 10071 Borgaro, Torino Tel: ++ 39 011 451 0111
IR JAPAN: K&H Bldg., 2F, 30-4 Nishi-Ikebukuro 3-Chome, Toshima-Ku, Tokyo 171 Tel: 81 (0)3 3983 0086
IR SOUTHEAST ASIA: 1 Kim Seng Promenade, Great World City West Tower, 13-11, Singapore 237994 Tel: ++ 65 (0)838 4630
IR TAIWAN: 16 Fl. Suite D. 207, Sec. 2, Tun Haw South Road, Taipei, 10673 Tel: 886-(0)2 2377 9936
Data and specifications subject to change without notice. 3/00